



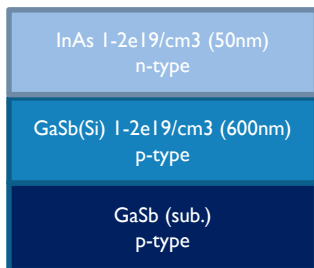
# imec

GROWTH PROPOSAL IEMN-IMEC

SALIM EL KAZZI, 3<sup>RD</sup> OCTOBER 2016

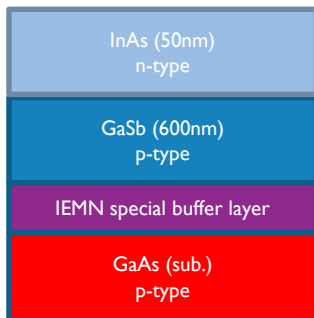
# SAMPLE DETAILS

## 3 samples

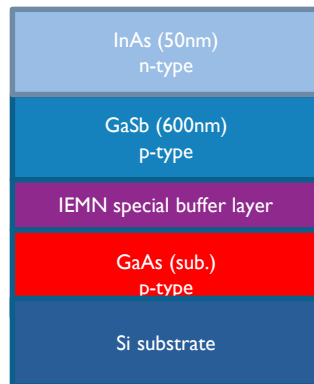


- InSb interface same temperature for n and p (This will be used for the growth on mismatched substrates)
- InSb interface different temperature between n and p (Si shutter open) (this is already done at IMEC please check some layer characterization in the 2nd slide)
- GaAs interface same temperature for n and p

## 1 sample



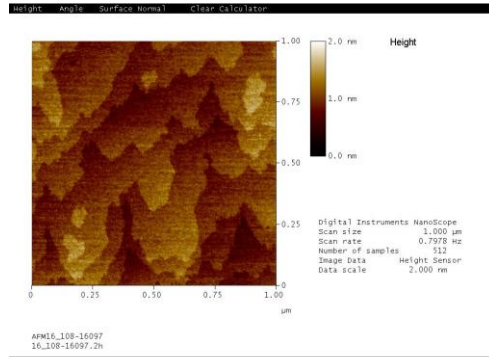
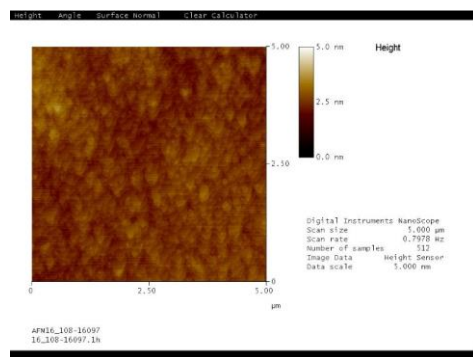
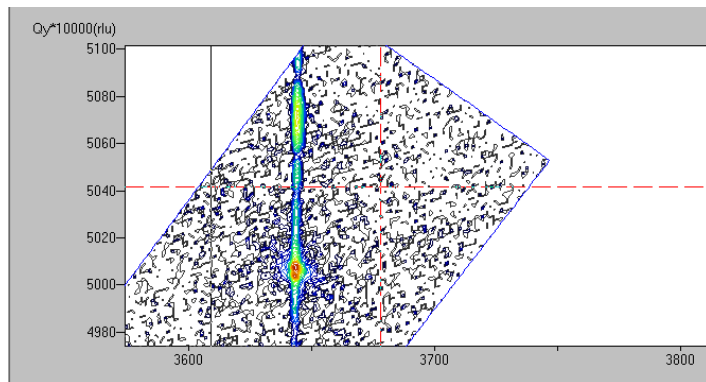
## 2 samples



- GaAs/Si with APD
- GaAs/Si w/o APD

# SAMPLE ALREADY GROWN AT IMEC

InAs 1-2e19/cm3 (50nm) n-type
GaSb(Si) 1-2e19/cm3 (600nm) p-type
GaSb (sub.) p-type



## MEETING MINUTES IMEC-IEMN 3<sup>RD</sup> OCTOBER 2016

- IEMN group agreed to grow the samples for imec and confirm their capability to grow the layers
- Imec received a reduced price since it's a joint research project between which interest both parties. Every publication would include the 2 groups.
- IEMN gave an estimation time to finish the growth for the end of October
- Actions:
  - Xavier will send the quotation to imec soon
  - Salim El Kazzi to check with Robert Langer on GaSb samples to send them together with Clement Merckling's GaAs/Si templates.



embracing a better life